SPP6308

DESCRIPTION

The SPP6308 is the Dual P-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

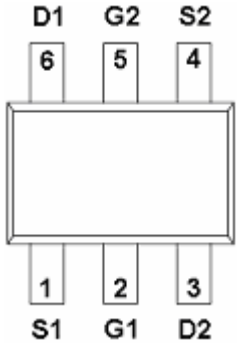
APPLICATIONS

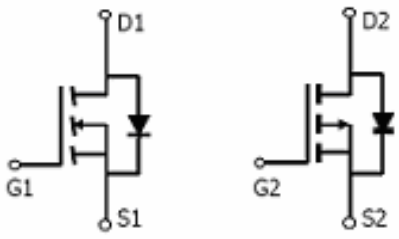
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

FEATURES

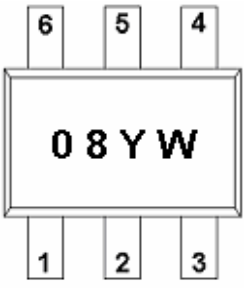
- P-Channel
  -20V/1.0A,$R_{DS(ON)}$= 520mΩ@V_{GS}=-4.5V
  -20V/0.8A,$R_{DS(ON)}$= 700mΩ@V_{GS}=-2.5V
  -20V/0.7A,$R_{DS(ON)}$= 950mΩ@V_{GS}=-1.8V
- Super high density cell design for extremely low RDS (ON)
- Exceptional on-resistance and maximum DC current capability
- SOT-363 (SC-70-6L) package design

PIN CONFIGURATION(SOT-363 / SC-70-6L)





PART MARKING



Y : Year Code
W: Week Code

SPP6308

PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP6308S36RG	SOT-363	08YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)
※ SPP6308S36RG : Tape Reel ; Pb – Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-1.0	A
	T_A=80℃		-0.7	
Pulsed Drain Current		I_{DM}	-3	A
Continuous Source Current(Diode Conduction)		I_S	-0.6	A
Power Dissipation	T_A=25℃	P_D	0.35	W
	T_A=70℃		0.19	
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient	T ≤ 10sec	$R_{\theta JA}$	360	℃/W
	Steady State		400	

SPP6308

ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.35		-0.8	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V			-1	uA
		V_{DS}=-20V,V_{GS}=0V T_J=55℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≤ -4.5V,V_{GS} =-5V	-2			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-1.0A		0.42	0.52	Ω
		V_{GS}=-2.5V,I_D=-0.8A		0.58	0.70	
		V_{GS}=-1.8V,I_D=-0.5A		0.75	0.95	
Forward Transconductance	gfs	V_{DS}=-10V,I_D=-1.0A		1.5		S
Diode Forward Voltage	V_{SD}	I_S=-0.5A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS} = -10V, V_{GS} = -4.5 V I_D = -0.88 A		1.5	2.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.2		
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V f=1MHz		145		pF
Output Capacitance	C_{oss}			25		
Reverse Transfer Capacitance	C_{rss}			10		
Turn-On Time	$t_{d(on)}$	V_{DD}=-10V,R_L=20Ω , I_D≡-0.5A V_{GEN}=-4.5V ,R_G=6Ω		18	30	ns
	t_r			25	40	
Turn-Off Time	$t_{d(off)}$			15	45	
	t_f			12	20	